L Number	Hits	Search Text	DB	Time stamp
_ Number	1	("20020037462").PN.	USPAT;	2003/01/21 11:31
İ			US-PGPUB	2003/03/31 15:25
-	2	(("6051349") or ("5968691")).PN.	USPAT; US-PGPUB	2003/03/31 13:23
Ì	0.0	(("6541170") or ("6457882") or ("6431769")	USPAT;	2003/04/01 17:47
-	28	or ("6281962") or ("6266125") or	US-PGPUB	
		("6221787") or ("5845170") or ("5939130")		
		or ("6543080") or ("6492271") or		
		("5879854") or ("6185472") or ("6001461")		
		or ("5817174") or ("6436723") or		
		("6431185") or ("6010797") or ("6118280")		
		or ("5485549") or ("6398429") or ("5908657") or ("6444029") or ("6033475")		
		or ("6023084") or ("5831300") or		
		("5933726") or ("5933724") or ("5804479")		
ļ		or ("5937290")).PN.	l	(0.1/01 10 00
_	13	((("6541170") or ("6457882") or	USPAT;	2003/04/01 18:32
		("6431769") or ("6281962") or ("6266125")	US-PGPUB	
		or ("6221787") or ("5845170") or		1
		("5939130") or ("6543080") or ("6492271") or ("5879854") or ("6185472") or		
		("6001461") or ("5817174") or ("6436723")		
,		or ("6431185") or ("6010797") or		
		("6118280") or ("5485549") or ("6398429")		,
		or ("5908657") or ("6444029") or		
		("6033475") or ("6023084") or ("5831300")		
		or ("5933726") or ("5933724") or ("5804479") or ("5937290")).PN.) and		
		((spin\$4 or rotat\$3 or centrifug\$3) and		
		(expos\$3 or radiat\$3 or irradiat\$3 or		
ì		light\$3) and develop\$3) same (resist or		
		photoresist or photosens\$5 or		
		photopolymer\$7)	USPAT;	2003/04/01 18:34
_	1695	430/22,30,311,313,322,330.ccls. and (((spin\$4 or rotat\$3 or centrifug\$6) and	US-PGPUB;	2003/04/01 10:01
		(((spin\$4 or rotat\$5 or tentifitg\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or	EPO; JPO;	
		light\$3) and develop\$3) same (resist or	IBM TDB	
		photoresist or photosens\$5 or		
		photopolymer\$7))		2003/09/27 14:42
_	1589	(430/22,30,311,313,322,330.ccls. and	USPAT; US-PGPUB;	2003/03/21 14.42
		(((spin\$4 or rotat\$3 or centrifug\$6) and	EPO; JPO;	
		(expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or	IBM TDB	
		photoresist or photosens\$5 or	_	
		photopolymer\$7))) and ((etch\$3 or heat\$3		
		or bak\$3 or prebak\$3 or postbak\$3) same		
ì		(resist or photoresist or photosens\$5 or		
	600	photopolymer\$7)) (430/22,30.ccls. not ((((spin\$4 or rotat\$3	USPAT;	2003/09/27 14:58
-	603	or centrifug\$6) and (expos\$3 or radiat\$3	US-PGPUB;	
		or irradiat\$3 or light\$3) and develop\$3)	EPO; JPO;	
		same (resist or photoresist or photosens\$5	IBM_TDB	
		or photopolymer\$7))) and ((etch\$3 or		
		heat\$3 or bak\$3 or prebak\$3 or postbak\$3)		
		same (resist or photoresist or photosens\$5		
	100	or photopolymer\$7))) (430/30.ccls. not (430/22,30.ccls. not	USPAT;	2003/04/10 19:43
-	40	((((spin\$4 or rotat\$3 or centrifug\$6) and	US-PGPUB;	
		(expos\$3 or radiat\$3 or irradiat\$3 or	EPO; JPO;	
		light\$3) and develop\$3) same (resist or	IBM_TDB	
		photoresist or photosens\$5 or		
		photopolymer\$7))) and ((etch\$3 or heat\$3		
	1	or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or		
		photopolymer\$7)))) and ((accelerat\$4 or		
		speed\$3 or rotat\$4 or spin\$4) same (resist		
		or photoresist or photosens\$5 or		
		photopolymer\$7) same (nozzle or pipe or	1	
1 .		spread\$3 or dispens\$3 or flow\$3))		

	0	(430/30.ccls. not (430/22,30.ccls. not	USPAT;	2003/04/12 12:54
	•	((((spin\$4 or rotat\$3 or centrifug\$6) and	US-PGPUB;	
	1	(expos\$3 or radiat\$3 or irradiat\$3 or	EPO; JPO;	
		light\$3) and develop\$3) same (resist or	IBM_TDB	
	İ	photoresist or photosens\$5 or		
		photopolymer\$7))) and ((etch\$3 or heat\$3		
		or bak\$3 or prebak\$3 or postbak\$3) same		
1		(resist or photoresist or photosens\$5 or		
		photopolymer\$7)))) and ((accelerat\$4 or		
		speed\$3 or rotat\$4 or spin\$4) same (resist		
		or photoresist or photosens\$5 or		
		photopolymer\$7) same (nozzle or pipe or		
		spread\$3 or dispens\$3 or flow\$3)) not		
		(430/22,30,311,313,322,330.ccls. and		
		(((spin\$4 or rotat\$3 or centrifug\$6) and		
		(expos\$3 or radiat\$3 or irradiat\$3 or		
		light\$3) and develop\$3) same (resist or		
		photoresist or photosens\$5 or		
		photopolymer\$7))) and ((etch\$3 or heat\$3		
		or bak\$3 or prebak\$3 or postbak\$3) same		ĺ
		(resist or photoresist or photosens\$5 or		
		photopolymer\$7))		
_	5	427/8-10 not	USPAT;	2003/09/27 15:12
-	5	(430/22,30,311,313,322,330.ccls. and	US-PGPUB;	
		(((spin\$4 or rotat\$3 or centrifug\$6) and	EPO; JPO;	
		(expos\$3 or radiat\$3 or irradiat\$3 or	IBM TDB	
		light\$3) and develop\$3) same (resist or	_	
1		photoresist or photosens\$5 or		
		photopolymer\$7))) and ((etch\$3 or heat\$3		
	ļ	or bak\$3 or prebak\$3 or postbak\$3) same		
		(resist or photoresist or photosens\$5 or		
		photopolymer\$7)) not (430/22,30.ccls. not		
		((((spin\$4 or rotat\$3 or centrifug\$6) and		
		(expos\$3 or radiat\$3 or irradiat\$3 or		
		light\$3) and develop\$3) same (resist or		
		photoresist or photosens\$5 or		
		photopolymer\$7))) and ((etch\$3 or heat\$3		
		or bak\$3 or prebak\$3 or postbak\$3) same		
		(resist or photoresist or photosens\$5 or		
		photopolymer\$7)))		
	66	(substrate or wafer) near3 (defect or	USPAT;	2003/09/27 15:12
_		fault) same (nozzle or pipe or spread\$3 or	US-PGPUB;	
		flow\$3 or dispens\$3) same (resist or	EPO; JPO;	
		photoresist or photosens\$5 or	IBM TDB	
		photopolymer\$7)		
	1	"5489337".PN.	USPAT;	2003/04/11 09:53
	1	310300 1240	US-PGPUB	
_	1	"5912054".PN.	USPAT;	2003/04/11 10:22
	**		US-PGPUB	
]_	1	("5409538").PN.	USPAT;	2003/04/11 16:07
		· · · · · · · · · · · · · · · · · · ·	US-PGPUB	
_	102	427/8-10.ccls. not	USPAT;	2003/04/14 12:48
		(430/22,30,311,313,322,330.ccls. and	US-PGPUB;	
}		(((spin\$4 or rotat\$3 or centrifug\$6) and	EPO; JPO;	
		(expos\$3 or radiat\$3 or irradiat\$3 or	IBM_TDB	
		light\$3) and develop\$3) same (resist or		
		photoresist or photosens\$5 or		
		photopolymer\$7))) and ((etch\$3 or heat\$3		
		or bak\$3 or prebak\$3 or postbak\$3) same		
		(resist or photoresist or photosens\$5 or		
		photopolymer\$7)) not (430/22,30.ccls. not		
		((((spin\$4 or rotat\$3 or centrifug\$6) and		
		(expos\$3 or radiat\$3 or irradiat\$3 or		
		light\$3) and develop\$3) same (resist or		
		photoresist or photosens\$5 or		
		photopolymer\$7))) and ((etch\$3 or heat\$3		
		or bak\$3 or prebak\$3 or postbak\$3) same		
		(resist or photoresist or photosens\$5 or		
		photopolymer\$7)))		

		in to the state of photorogist)	USPAT;	2003/09/27 15:36
-	10	427/8-10.ccls. and (resist or photoresist)	US-PGPUB;	2003/03/2/ 13:30
		same (nozzle or dispens\$3 or spread\$3 or	EPO; JPO;	
		pip\$3 or eject\$3) near3 (accelerat\$3 or		
		decelerat\$3 or position\$3 or location)	IBM_TDB	2003/09/27 15:37
_	10	427/8-10.ccls. and (resist or photoresist)	USPAT;	2003/09/2/ 15:3/
		same (nozzle or dispens\$3 or spread\$3 or	US-PGPUB;	
		nip\$3 or eject\$3) same (accelerat\$3 or	EPO; JPO;	
		decelerat\$3 or position\$3 or location) not	IBM_TDB	ļ.
		(427/8-10.ccls, and (resist or		
		photoresist) same (nozzle or dispens\$3 or		
		spread\$3 or pip\$3 or eject\$3) near3		1
		(accelerat\$3 or decelerat\$3 or position\$3		
		or location))		
	1		USPAT;	2003/04/14 15:52
. –	1	"4451507".PN.	US-PGPUB	
			USPAT;	2003/04/14 15:59
-	1	"5500243".PN.		2003/04/14 13:33
			US-PGPUB	2003/04/14 16:00
_	1	"5843527".PN.	USPAT;	2003/04/14 16:00
			US-PGPUB	
_	1332	430/30.ccls. not (430/22,30.ccls. not	USPAT;	2004/04/28 17:50
		((((spin\$4 or rotat\$3 or centrifug\$6) and	US-PGPUB;	
		(expos\$3 or radiat\$3 or irradiat\$3 or	EPO; JPO;	
		light\$3) and develop\$3) same (resist or	IBM_TDB	
		photoresist or photosens\$5 or	_	
		photopolymer\$7))) and ((etch\$3 or heat\$3		
		or bak\$3 or prebak\$3 or postbak\$3) same		
		(resist or photoresist or photosens\$5 or		
		photopolymer\$7)))	USPAT;	2004/04/28 17:46
	23	430/22,30,311,313,322,330.ccls. and	US-PGPUB;	2001, 01, 20 11110
		((contribut\$6 near3 degree or proportion		
		or coefficien\$3 or factor\$3 or amount\$3 or	EPO; JPO;	
		percent\$3 or relativ\$3 or grad\$3 or	IBM_TDB	
		level\$3 or exten\$4) same (resist or		
i		photoresist) same (thick\$4 and temperature		
		and pressure and (humidi\$5 or moistur\$6 or		
		wet\$4)))		
_	1725	(430/22,30,311,313,322,330.ccls. and	USPAT;	2004/04/28 17:45
		(((spin\$4 or rotat\$3 or centrifug\$6) and	US-PGPUB;	
		(expos\$3 or radiat\$3 or irradiat\$3 or	EPO; JPO;	
		light\$3) and develop\$3) same (resist or	IBM TDB	
		photoresist or photosens\$5 or	_	1
		photopolymer\$7))) and ((etch\$3 or heat\$3		
		or bak\$3 or prebak\$3 or postbak\$3) same		
		(resist or photoresist or photosens\$5 or		
		(resist or photoresist or photosensys or		4
		photopolymer\$7)) not (		
		430/22,30,311,313,322,330.ccls. and		
1		((contribut\$6 near3 degree or proportion		
		or coefficien\$3 or factor\$3 or amount\$3 or		
		percent\$3 or relativ\$3 or grad\$3 or		
		level\$3 or exten\$4) same (resist or		
		photoresist) same (thick\$4 and temperature		171
		and pressure and (humidi\$5 or moistur\$6 or		
		wet\$4))))		
1 _	671	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2004/04/28 17:44
-	0/1	or centrifug\$6) and (expos\$3 or radiat\$3	US-PGPUB;	
	1	or irradiat\$3 or light\$3) and develop\$3)	EPO; JPO;	
		same (resist or photoresist or photosens\$5	IBM TDB	
		Same (resist of photoresist of photosensys	1	,
		or photopolymer\$7))) and ((etch\$3 or	1	
		heat\$3 or bak\$3 or prebak\$3 or postbak\$3)	1	
	1	same (resist or photoresist or photosens\$5		
1	1	or photopolymer\$7)))		

				0004/04/00 17:43
-	5	427/8-10 not	USPAT; US-PGPUB;	2004/04/28 17:43
		(430/22,30,311,313,322,330.ccls. and (((spin\$4 or rotat\$3 or centrifug\$6) and	EPO; JPO;	
		(((spin\$4 or rotat\$3 or centifitug\$0) and (expos\$3 or radiat\$3 or irradiat\$3 or	IBM TDB	
		light\$3) and develop\$3) same (resist or		
		photoresist or photosens\$5 or		
		photopolymer\$7))) and ((etch\$3 or heat\$3		
		or bak\$3 or prebak\$3 or postbak\$3) same		
		(resist or photoresist or photosens\$5 or		
		photopolymer\$7)) not (430/22,30.ccls. not		
		(((spin\$4 or rotat\$3 or centrifug\$6) and		
		(expos\$3 or radiat\$3 or irradiat\$3 or		
		light\$3) and develop\$3) same (resist or		
		photoresist or photosens\$5 or		ĺ
		photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same		
		(resist or photoresist or photosens\$5 or	İ	
		photopolymer\$7)))		
	71	(substrate or wafer) near3 (defect or	USPAT;	2004/04/28 17:42
-	/ 1	fault) same (nozzle or pipe or spread\$3 or	US-PGPUB;	
		flow\$3 or dispens\$3) same (resist or	EPO; JPO;	
	1	photoresist or photosens\$5 or	IBM_TDB	
		photopolymer\$7)	110571	2004/04/20 17:41
_	13	427/8-10.ccls. and (resist or photoresist)	USPAT;	2004/04/28 17:41
		same (nozzle or dispens\$3 or spread\$3 or	US-PGPUB; EPO; JPO;	
		pip\$3 or eject\$3) near3 (accelerat\$3 or decelerat\$3 or position\$3 or location)	IBM TDB	
	1.0	427/8-10.ccls. and (resist or photoresist)	USPAT;	2004/04/28 17:37
_	12	same (nozzle or dispens\$3 or spread\$3 or	US-PGPUB;	2001,01,01
		pip\$3 or eject\$3) same (accelerat\$3 or	EPO; JPO;	
		decelerat\$3 or position\$3 or location) not	IBM_TDB	
		(427/8-10.ccls. and (resist or	_	
		photoresist) same (nozzle or dispens\$3 or		
		spread\$3 or pip\$3 or eject\$3) near3		
		(accelerat\$3 or decelerat\$3 or position\$3		
		or location))	USPAT;	2004/04/28 17:33
-	8	(427/8-10 or 438/5-18).ccls. and ((contribut\$6 near3 degree or proportion	US-PGPUB;	2004/04/20 17.33
		or coefficien\$3 or factor\$3 or amount\$3 or	EPO; JPO;	
		percent\$3 or relativ\$3 or grad\$3 or	IBM TDB	
		level\$3 or exten\$4) same (resist or	_	
		photoresist) same (thick\$4 and temperature		
		and pressure and (humidi\$5 or moistur\$6 or		
		wet\$4)))		
-	16	(427/8-10 or 438/5-18).ccls. and	USPAT;	2004/04/28 17:23
		(formula\$1 or equation) same (resist or	US-PGPUB; EPO; JPO;	
		photoresist) same thick\$4 not	IBM TDB	
		((contribut\$6 near3 degree or proportion or coefficien\$3 or factor\$3 or amount\$3 or	TBH_TBB	
		percent\$3 or relativ\$3 or grad\$3 or		
		level\$3 or exten\$4) same (resist or		†
		photoresist) same (thick\$4 and temperature		!
		and pressure and (humidi\$5 or moistur\$6 or		
		wet\$4)))		0004/04/00 27 67
-	51	(430/22,30 or 438/5-18).ccls. and (etch\$3	USPAT;	2004/04/28 17:23
		near3 (line or pattern) same (alarm\$3 or	US-PGPUB; EPO; JPO;	
		alert\$3 or warn\$3 or buzz\$3 or signal\$4 or	IBM TDB	
	, ,,,	notif\$4)) semiconduct\$3 and (etch\$3 same (alarm\$3 or	USPAT;	2004/04/28 17:22
_	75	alert\$3 or warn\$3 or buzz\$3 or notif\$4)	US-PGPUB;	,
		same (operator or human3 or manual\$3 or	EPO; JPO;	
		person\$6 or eye\$3))	IBM_TDB	
_	83	semiconduct\$3 and (etch\$3 same (alarm\$3 or	USPAT;	2004/04/28 17:23
		alert\$3 or warn\$3 or buzz\$3 or notif\$4)	US-PGPUB;	
		same (operator or human3 or manual\$3 or	EPO; JPO;	
		person\$6 or eye\$3))	IBM_TDB USPAT;	2004/04/28 17:23
_	61	(430/22,30 or 438/5-18).ccls. and (etch\$3	US-PGPUB;	2007/04/20 11.23
		near3 (line or pattern) same (alarm\$3 or alert\$3 or warn\$3 or buzz\$3 or signal\$4 or	EPO; JPO;	
		notif\$4))	IBM TDB	
		INOCTIVAI)		

		· <del></del>		
_	19	(427/8-10 or 438/5-18).ccls. and (formula\$1 or equation) same (resist or photoresist) same thick\$4 not	USPAT; US-PGPUB; EPO; JPO;	2004/04/28 17:24
		((contribut\$6 near3 degree or proportion or coefficien\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or	IBM_TDB	
		level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature		
	8	and pressure and (humidi\$5 or moistur\$6 or wet\$4))) (427/8-10 or 438/5-18).ccls. and	USPAT;	2004/04/28 17:33
_	8	((contribut\$6 near3 degree or proportion or coefficien\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or	US-PGPUB; EPO; JPO; IBM_TDB	
		level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4)))		
_	12	427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) same (accelerat\$3 or	USPAT; US-PGPUB; EPO; JPO;	2004/04/28 17:37
		decelerat\$3 or position\$3 or location) not (427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or	IBM_TDB	
		spread\$3 or pip\$3 or eject\$3) near3 (accelerat\$3 or decelerat\$3 or position\$3 or location))		2004/04/28 17:41
	14	427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) near3 (accelerat\$3 or decelerat\$3 or position\$3 or location)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	
-	89	(substrate or wafer) near3 (defect or fault) same (nozzle or pipe or spread\$3 or flow\$3 or dispens\$3) same (resist or photoresist or photosens\$5 or	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/04/28 17:43
_	5	photopolymer\$7) 427/8-10 not (430/22,30,311,313,322,330.ccls. and (((spin\$4 or rotat\$3 or centrifug\$6) and	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/04/28 17:43
		<pre>(expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3</pre>		
		or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)) not (430/22,30.ccls. not ((((spin\$4 or rotat\$3 or centrifug\$6) and		
		(expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or	*	
		photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or		
_	773	photopolymer\$7))) (430/22,30.ccls. not ((((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3)	USPAT; US-PGPUB; EPO; JPO;	2004/04/28 17:44
		same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3)	IBM_TDB	
		<pre>same (resist or photoresist or photosens\$5 or photopolymer\$7)))</pre>		

			TIODAM -	2004/04/28 17:46
_	1950	(430/22,30,311,313,322,330.ccls. and	USPAT;	2004/04/28 17.40
		(((spin\$4 or rotat\$3 or centrifug\$6) and	US-PGPUB;	
		(expos\$3 or radiat\$3 or irradiat\$3 or	EPO; JPO;	
		light\$3) and develop\$3) same (resist or	IBM_TDB	
		photoresist or photosens\$5 or		
		photopolymer\$7))) and ((etch\$3 or heat\$3		
		or bak\$3 or prebak\$3 or postbak\$3) same		
		(resist or photoresist or photosens\$5 or		
		photopolymer\$7)) not (		
	Ì	430/22,30,311,313,322,330.ccls. and		
		((contribut\$6 near3 degree or proportion		
		or coefficien\$3 or factor\$3 or amount\$3 or		1
		percent\$3 or relativ\$3 or grad\$3 or		
		level\$3 or exten\$4) same (resist or		
		photoresist) same (thick\$4 and temperature		
		and pressure and (humidi\$5 or moistur\$6 or		
	1	wet\$4)))))		
_	23	430/22,30,311,313,322,330.ccls. and	USPAT;	2004/04/28 17:47
		((contribut\$6 near3 degree or proportion	US-PGPUB;	
		or coefficien\$3 or factor\$3 or amount\$3 or	EPO; JPO;	
		percent\$3 or relativ\$3 or grad\$3 or	IBM_TDB	
		level\$3 or exten\$4) same (resist or		
		photoresist) same (thick\$4 and temperature		
		and pressure and (humidi\$5 or moistur\$6 or		
		wet\$4)))		
	1	1		